New Jersey Semi-Conductor Products, Inc.

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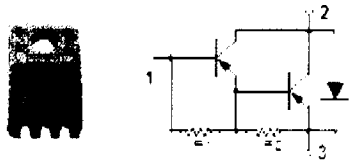
Silicon PNP Darlington Power Transistor — 2SB1226

DESCRIPTION

- High DC Current Gain-
  : h_{FE} 1500(Min)@ (V_{CE}= -3V, I_C= -1:5A)
- Large Current Capability and Wide ASO.
- Complement to Type 2SD1828

APPLICATIONS

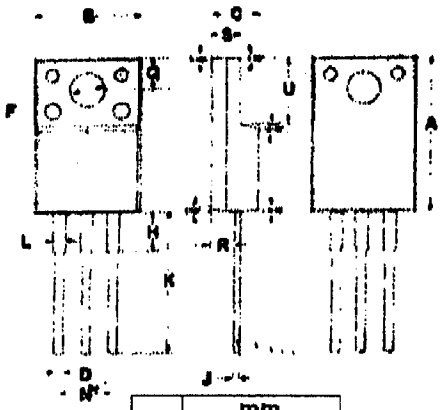
- Designed for use in control of motor drivers, printer hammer drivers, and constant-voltage regulators.



PIN: 1 Base
2 Collector
3 Emitter
TO-220F package

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-110	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Peak	-5	A
P_C	Collector Power Dissipation @T_a=25℃	2	W
	Collector Power Dissipation @T_C=25℃	20	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	mm MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

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Quality Semi-Conductors

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA; R_{BE}= ∞	-100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -5mA; I_E= 0	-110			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -1.5A; I_B= -3mA			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -1.5A; I_B= -3mA			-2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -80V; I_E= 0			-100	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-3.0	mA
h_{FE}	DC Current Gain	I_C= -1.5A; V_{CE}= -3V	1500			
f_T	Current-Gain—Bandwidth Product	I_C= -1.5A; V_{CE}= -5V		20		MHz

Switching Times

t_{on}	Turn-on Time	I_C= -1A, I_{B1}= -I_{B2}= -2mA, V_{CC}= -50V; R_L= 50Ω		0.7		μ s
t_{stg}	Storage Time			2.4		μ s
t_f	Fall Time			1.2		μ s